Absolute Maximum Ratings

Symbol	Conditions [1]	Values	Units
V_{DS}		500	V
V_{DGR}	R_{GS} = 20 kΩ	500	V
I_D		56	A
I_{DM}		224	A
V_{GS}		± 20	V
P_D		700	W
T_j, T_{stg}		– 55 . . .+150	°C
V_{isol}	AC, 1 min	2 500	V
humidity	DIN 40 040	Class F	
climate	DIN IEC 68 T.1	55/150/56	
Inverse Diode			
I_F= – I_D		56	A
I_{FM}= – I_{DM}		224	A

Characteristics

Symbol	Conditions [1]	min.	typ.	max.	Units
$V_{(BR)DSS}$	V_{GS} = 0, I_D = 0,25 mA	500	–	–	V
$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 1 mA	2,1	3,0	4,0	V
I_{DSS}	V_{GS} = 0, T_j = 25 °C	–	50	250	µA
	V_{DS} = 500 V, T_j = 125 °C	–	300	1000	µA
I_{GSS}	V_{GS} = 20 V, V_{DS} = 0	–	10	100	nA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 36 A	–	90	110	mΩ
g_{fs}	V_{DS} = 25 V, I_D = 36 A	20	30	–	S
C_{CHC}		–	–	160	pF
C_{iss}	V_{GS} = 0	–	22	30	nF
C_{oss}	V_{DS} = 25 V	–	1,6	2,4	nF
C_{rss}	f = 1 MHz	–	0,6	1	nF
L_{DS}		–	–	20	nH
$t_{d(on)}$	V_{DD} = 250 V	–	60	–	ns
t_r	I_D = 36 A	–	35	–	ns
$t_{d(off)}$	V_{GS} = 10 V	–	350	–	ns
t_f	R_{GS} = 3,3 Ω	–	70	–	ns
Inverse Diode					
V_{SD}	I_F = 110 A, V_{GS} = 0	–	1,3	1,6	V
t_{rr}	T_j = 25 °C [2]	–	200	280	ns
	T_j = 150 °C [2]	–	350	500	ns
Q_{rr}	T_j = 25/150 °C [2]	–	1,5/8,5	2,5/12	µC
I_{RRM}	T_j = 25/150 °C [2]	–	12/28	–	A
Thermal Characteristics					
R_{thjc}		–	–	0,18	°C/W
R_{thch}	M_1, surface 10 µm	–	–	0,05	°C/W

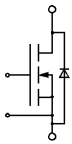
Mechanical Data

M_1	to heatsink, SI Units	4	–	6	Nm
	to heatsink, US Units	35	–	53	lb.in.
M_2	for terminals, SI Units	2,5	–	3,5	Nm
	for terminals, US Units	22	–	24	lb.in.
a		–	–	5x9,81	m/s^2
w		–	–	150	g
Case	→ page B 5 – 2		D 15		

[1] T_{case} = 25 °C, unless otherwise specified.
[2] I_F = – I_D, V_R = 100 V, – di_F/dt = 100 A/µs

SEMITRANS® M
Power MOSFET Modules
SKM 151 F

SEMITRANS M1



Features

- N Channel, enhancement mode
- Fast inverse diode
- Short internal connections avoid oscillations
- Switching kW's in less than 1 µs
- Isolated copper baseplate
- All electrical connections on top for easy busbaring
- Large clearances and creepage distances
- UL recognized, file no. E 63 532

Typical Applications

- Switched mode power supplies
- DC servo and robot drives
- DC choppers
- Resonant and welding inverters
- Induction heaters
- AC motor drives
- Laser power supplies
- UPS equipment
- Plasma cutting
- Not suitable for linear amplification

This is an electrostatic discharge sensitive device (ESDS). Please observe the international standard IEC 747-1, Chapter IX.

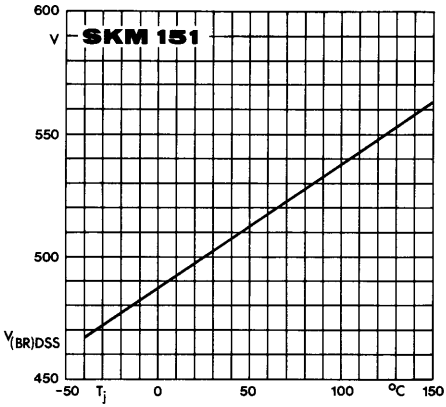


Fig. 7 Breakdown voltage vs. temperature

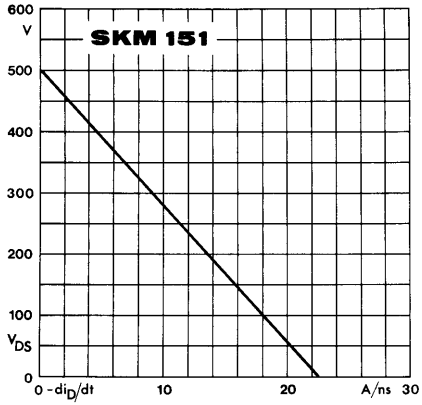


Fig. 8 Drain-source voltage derating

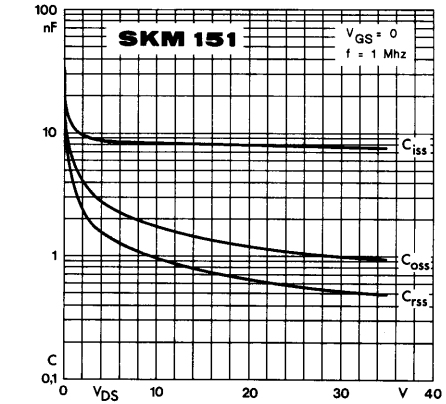


Fig. 9 Capacitances vs. drain-source voltage

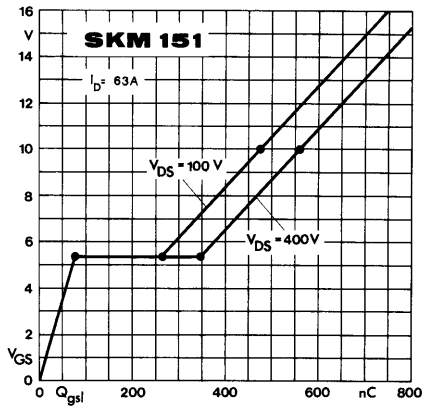


Fig. 10 Gate charge characteristic

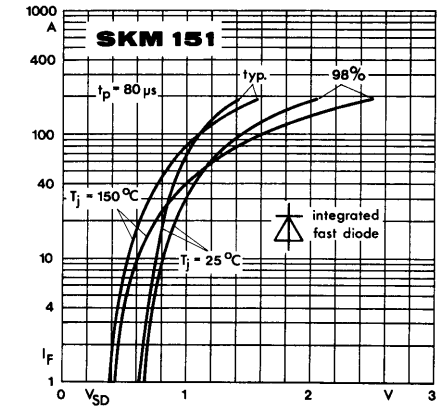


Fig. 11 Diode forward characteristic

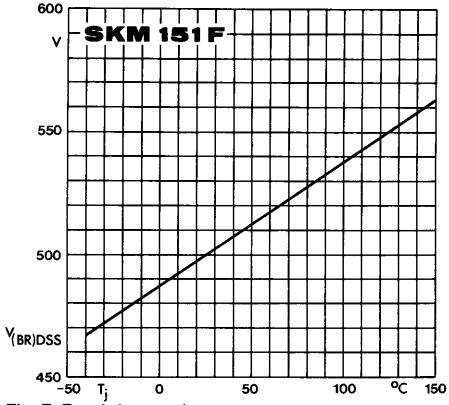


Fig. 7 Breakdown voltage vs. temperature

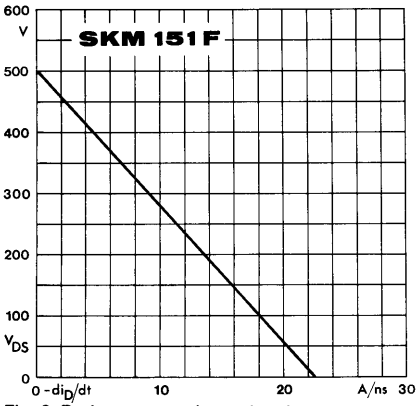


Fig. 8 Drain-source voltage derating

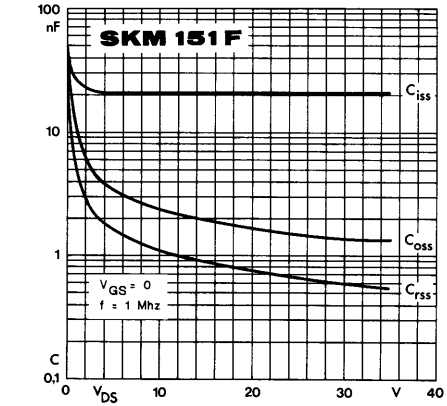


Fig. 9 Capacitances vs. drain-source voltage

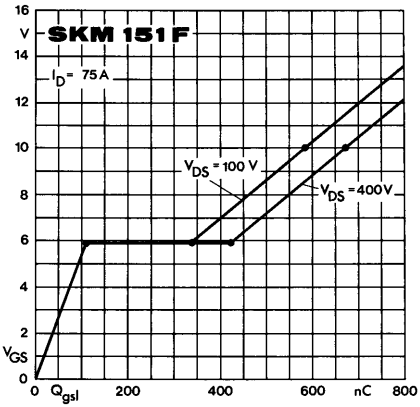


Fig. 10 Gate charge characteristic

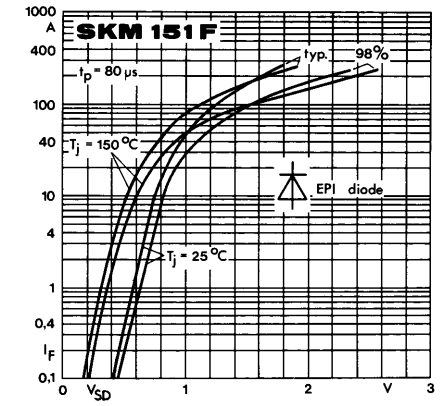


Fig. 11 Diode forward characteristic

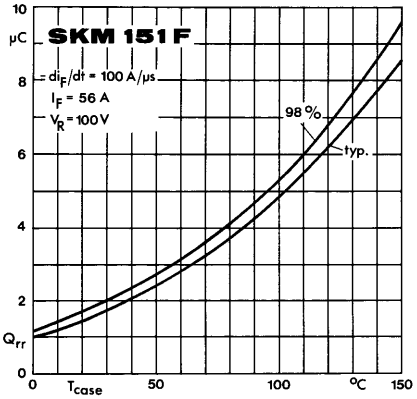


Fig. 12 Diode recovered charge

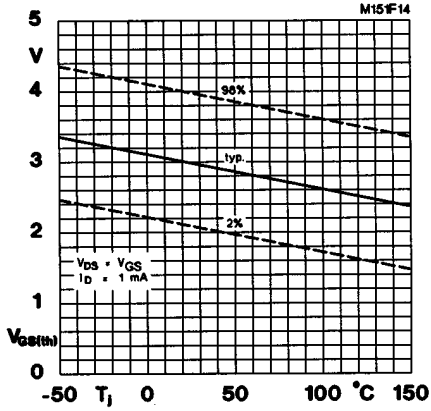


Fig. 14 Gate-source threshold voltage

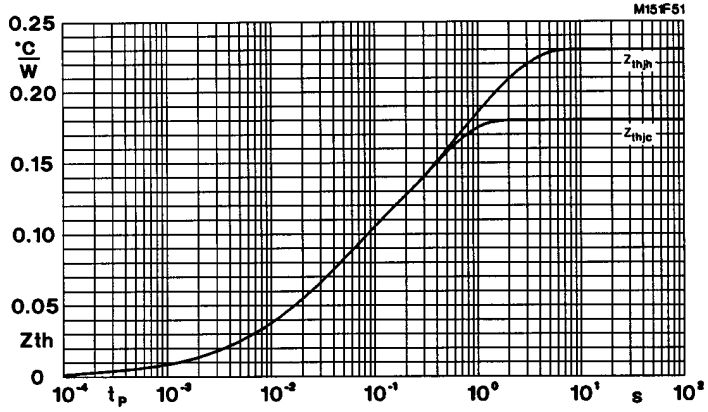


Fig. 51 Transient thermal impedance

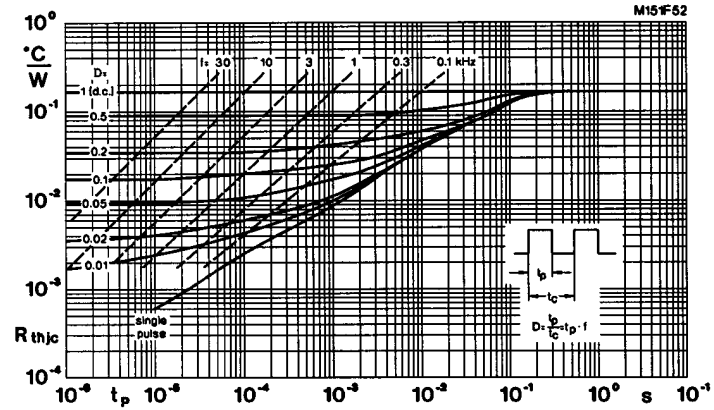


Fig. 52 Thermal impedance under pulse conditions

